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Inc	losure	Material	:

Metal

**Overall Length:** 

1.453 inches

# Terminal Length:

0.450 inches

## **Overall Diameter:**

0.667 inches

# **Mounting Facility Quantity:**

1

# Mounting Method:

Threaded stud

#### Cubic Measure:

2.030 cubic inches

#### Thready Qty Per Inch (tpi):

28

#### Thread Size:

0.125 inches

## **Criticality Code Justification:**

Feat

## Semiconductor Material:

Silicon

# Voltage Rating In Volts Per Characteristic:

400.0 emitter to collector voltage, floating potential, dc with base biased in reverse direction with respect to the collector

## **Current Rating Per Characteristic:**

50.00 amperes peak forward surge current megahertz

#### **Power Rating Per Characteristic:**

50.0 watts small-signal input power, common-collector preset

#### Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

#### **Special Features:**

Nuclear hardness critical item; junction pattern arrangement: pn

#### **Thread Series Designator:**

Unf

#### **Terminal Type And Quantity:**

1 threaded stud and 1 tab, solder lug

Shelf Life:

N/a

## Unit Of Measure:

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#### Demilitarization:

No

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